

Band-switching diodes

BA482; BA483; BA484

FEATURES

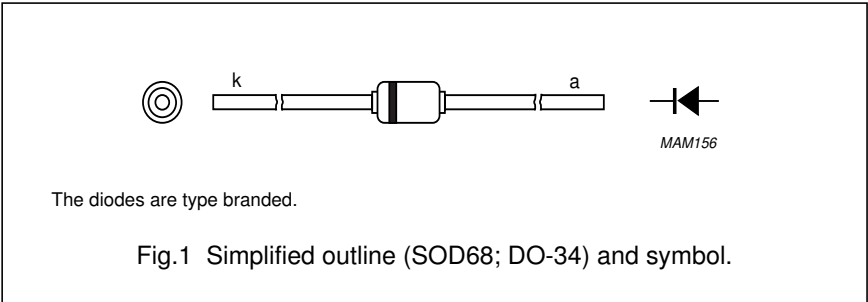
- Continuous reverse voltage:
max. 35 V
- Continuous forward current:
max. 100 mA
- Low diode capacitance:
max. 1.0 to 1.6 pF
- Low diode forward resistance:
max. 0.7 to 1.2 Ω.

APPLICATION

- VHF television tuners.

DESCRIPTION

Planar high performance band-switching diode in a hermetically sealed glass SOD68 (DO-34) package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _R	continuous reverse voltage	–	35	V
I _F	continuous forward current	–	100	mA
T _{stg}	storage temperature	–65	+150	°C
T _j	junction temperature	–	150	°C

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	I _F = 100 mA; see Fig.2	–	1.2	V
I _R	reverse current	see Fig.3 V _R = 20V V _R = 20 V; T _{amb} = 75 °C	– –	100 1	nA μA
C _d	diode capacitance BA482 BA483 BA484	f = 1 to 100 MHz; V _R = 3 V; see Fig.4	0.8 0.7 1.0	1.2 1.0 1.6	pF pF pF
r _D	diode forward resistance BA482 BA483 BA484	I _F = 3 mA; f = 200 MHz; see Fig.5	0.6 0.8 0.8	0.7 1.2 1.2	Ω Ω Ω

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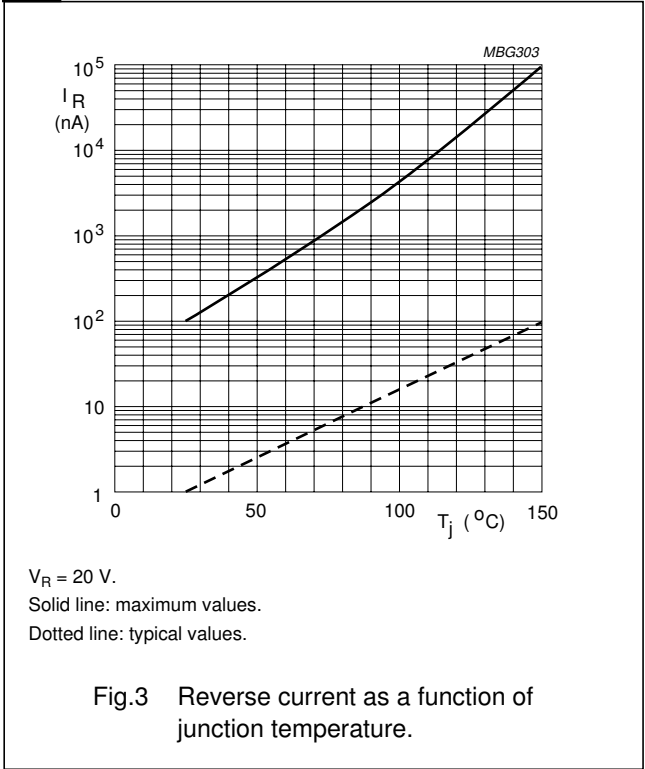
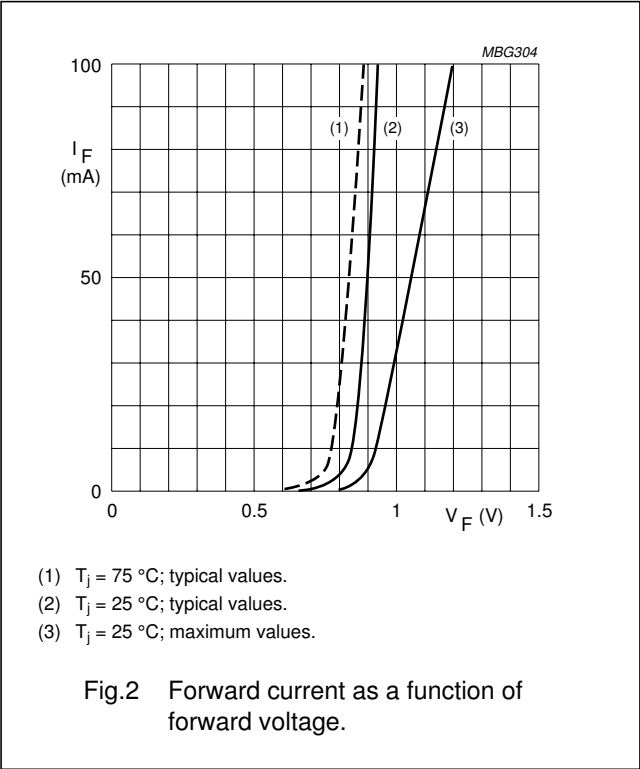
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point	lead length 10 mm	300	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

Note

1. Device mounted on a FR4 printed-circuit board without metallization pad.

GRAPHICAL DATA



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